Discovery of two families of VSb-based compounds with V-kagome lattice

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Abstract
Recently V-based kagome lattice AV$_3$Sb$_5$ (A=K, Rb, Cs), exhibiting topological characters, exotic charge density wave and superconductivity, have been attracting enormous attention in condensed matter physics. The origin of charge density wave and superconductivity remains elusive so far. This motives us to explore other families of VSb-based compounds containing V-kagome lattice, which is helpful to understand the relationship between structure and physical property. In this manuscript, we report the structure and physical property of two newly-discovered VSb-compounds CsV$_8$Sb$_{12}$ and CsV$_6$Sb$_6$ with C$_2$ (space group: Cmmm) and C$_3$ (space group: R-3m) symmetry, in which both compounds consist of the basic V-kagome unit. In CsV$_8$Sb$_{12}$, a rectangle V$_2$Sb$_2$ layer is sandwiched between two V$_3$Sb$_5$ layers, slightly distorting the V-kagome lattice and the structure turning to be orthorhombic type. In the latter one, a more complex slab consisted of two half-V$_3$Sb$_5$ layer is the basic unit that are intercalated by the Cs cations along the c-axis. Transport property measurements demonstrate that both compounds are metallic with carrier density around 10$^{21}$ cm$^{-3}$ and paramagnetic with small effective moment. No superconductivity has been observed in CsV$_8$Sb$_{12}$ above 2 K under in-situ pressure up to 51.1 GPa. Theoretical calculations and experimental measurements reveal a quasi-two-dimensional electronic structure with C$_2$ symmetry in CsV$_8$Sb$_{12}$ without van Hove singularities near the Fermi level, distinct from CsV$_3$Sb$_5$. Our study will stimulate more research about exploring new V-based kagome quantum materials.

Introduction
The kagome net, a corner-sharing tiling pattern of triangular plaquettes, is a fundamental model for studying nontrivial topology, frustrated magnetism and correlated phenomena. The frustrated lattice geometry endows a wealth of unique physical features to the recently intensely investigated kagome metals, including flat bands, van Hove singularity, and topological band crossover. Generally, pure kagome
layers cannot stand alone and are intergrown with other building blocks. The stacking induced interaction and charge donation bring rich varieties to the electronic properties that inherited from the kagome lattice. Prominent examples are noncollinear antiferromagnetism in Mn$_3$Sn$_2$ [1], Dirac fermionic in ferromagnetism in Fe$_3$Sn$_2$ [2], Chern-gapped Dirac fermion in ferromagnetic TbMn$_6$Sn$_6$ [3], and Weyl fermions in the ferromagnet Co$_3$Sn$_2$S$_2$ [4].

A fresh wave of interest is sparked by the seminal discovery of AV$_3$Sb$_5$ (A = K, Rb, Cs) [5,6]. The vanadium sublattice forms perfect kagome net, interwoven with Sb atoms within and out of the plane to produce a V$_3$Sb$_5$ monolayer, as illustrated in Fig. 1. The lack of magnetism endows the Z$_2$ topological AV$_3$Sb$_5$ with alternative ground states such as the charge density wave (CDW) ordering and superconductivity. This CDW ordering is later proved not driven by strong electron-phonon coupling [7–14] and compete with superconductivity [15]. Subsequent studies further discovered exciting discoveries including the reentrance of superconductivity under high pressure [16–19], large intrinsic anomalous Hall effect [20,21], pair density wave [11] and evidence of plausible unconventional superconductivity [11,22]. Given the very weak interlayer interactions, altering the staking sequence of the kagome layer with different building blocks and observing the effects on physical properties is both fascinating and technically possible. However, only partial removal A element has been realized through selective oxidation of thin flakes, resulting in shift of van Hove singularity [23,24], enhanced T$_c$ [15,25–28] and A-vacancy ordering [29]. Construction of novel vanadium-based kagome structure by varying the stacking sequence has not been realized so far.

Here, we explore the potential of constructing novel A-V-Sb compounds by altering the stacking of the constituent layers. As a consequence, two new family of compounds AV$_8$Sb$_{12}$ and AV$_6$Sb$_6$ (A = Rb, Cs) are discovered. By the insertion of different building blocks or stacking sequence, we find the initial C$_6$ symmetry is lowered to C$_2$ and C$_3$ in AV$_8$Sb$_{12}$ and AV$_6$Sb$_6$, respectively. This symmetry broken bring dramatic change towards their band structures. Theoretical calculation and ARPES measurements reveal unprecedented features compared to AV$_3$Sb$_5$.

**Experimental**

**Single crystal growth:** Single crystals of AV$_8$Sb$_{12}$ and AV$_6$Sb$_6$ (A = Cs, Rb) were grown via the self-flux method. For AV$_8$Sb$_{12}$, Cs (99.98%), V (powder, 99.99%) and Sb (ingot, 99.999%) were mixed with the molar ratio of 1.2:6:15, loaded into an alumina container and then sealed into a silica tube in vacuum. The mixture was subsequently heated to 1273 K and kept for 24 h, then cooled to 1173 K in 72 h. The excess flux was removed by centrifuging at 1173 K. For AV$_6$Sb$_6$, Cs (99.98%), V (powder, 99.99%) and Sb (ingot, 99.999%) were mixed with the molar ratio of 1.2:6:18, loaded into an alumina container and then sealed into a silica tube in vacuum. The mixture was subsequently heated to 1373 K and kept for 24 h, then cooled to 1273 K in 72 h. The excess flux was removed by centrifuging at 1273 K.
Characterization: The diffraction was performed on Panalytical X’pert diffractometer with a Cu Kα anode (1.5481 Å). The composition and structure of the sample were determined by the combination of EDS and scanning transmission electron microscope (STEM). The atomic arrangement of the two-phase was observed by spherical aberration corrected ARM200F (JEOL, Tokyo, Japan) STEM operated at 200 kV with a convergence angle of 25 mrad and collected angle from 70 to 250 mrad. The high angle annular dark field STEM (HAADF-STEM) image was collected with a dwell time of 10 µs each pixel. The transport measurement under ambient and high pressure was performed on Quantum Design Physical Property Measurement System (PPMS). A Keithley 2182A, a Keithley 6221 and a Keithley 2400 were used to measure the transport properties under external magnetic fields. Magnetization measurements were performed using a Quantum Design Magnetic Properties Measurement System (MPMS3). High pressure resistivity of CsV₈Sb₁₂ samples was measured by a diamond anvil cell (DAC) range from 2K to 400K with the van der Pauw method. The resistance experiments were performed using an Be–Cu cells. The cubic boron nitride (cBN) powders (200 and 300 nm in diameter) were employed as the medium to transfer pressure. The pressure was calibrated using the ruby fluorescence method at room temperature, whether before and after the measurement.

Computational: Our DFT calculations employ the projector augmented wave (PAW) method [30] encoded in Vienna ab initio simulation package (VASP) [31], and both the local density approximation (LDA) and generalized-gradient approximation (GGA) [32] for the exchange correlation functional are used. Throughout this work, the cutoff energy of 500 eV is taken for expanding the wave functions into plane-wave basis. In the calculation, the Brillouin zone is sampled in the k space within Monkhorst-Pack scheme [33]. The number of these k points is 9x9x5 for the primitive cell. We relax the lattice constants and internal atomic positions, where the plane wave cutoff energy is 600 eV. Forces are minimized to less than 0.01 eV/Å in the relaxation. The obtained lattice constants of CsV₈Sb₁₂ are \(a=9.515\) Å, \(b=5.455\) Å and \(c=18.25\) Å, which are in good agreement with experimental values \(a=9.516\) Å, \(b=5.451\) Å and \(c=18.128\) Å.

Results and discussions
From Figure 1, one can see that the structures of three A-V-Sb compounds share a similar basic unit of V-based kagome lattice plus a centered Sb atom. In the AV₃Sb₅s, the space group is \(P6/mmm\) with \(C₆\) symmetry, a V-based kagome lattice are sandwiched by two Sb honeycomb lattices. The lattice constants are \(a=5.4922\) Å and \(c=9.8887\) Å. The crystal structure is rather simple. However, in the newly-discovered two compounds, the crystal is more complex due to intercalation of low-symmetry structure unit V₂Sb₂ layer and V₅Sb₇. In AV₆Sb₁₂, an orthorhombic V₂Sb₂ layer is sandwiched by two V₅Sb₇ units, forming a V₈V₁₂ unit. The space group is Cmmmm with lattice constants of \(a=9.4510\) Å, \(b=9.5164\) Å and \(c=18.1582\) Å. The \(a\)-axis is close to \(\sqrt{3}\) times of that of AV₃Sb₅. As for AV₆Sb₁₂, the basic unit can be viewed as two-V₃Sb₅-connected slab with removing the center two Sb layers. Each half-V₃Sb₅ unit is shifted by \((1/2, 1/2, 0)\), and the whole slab is separated by a Cs atom along the \(c\)-axis. The space group is \(R-3m\) with lattice constants of \(a=5.3172\) Å and \(c=34.0741\) Å, in which
the \( c \)-axis is almost 3 times of \( c \)-axis of \( \text{AV}_3\text{Sb}_5 \). The latter two compounds \( \text{AV}_8\text{Sb}_{12} \) and \( \text{AV}_6\text{Sb}_6 \) can be viewed as derivative phases based on \( \text{AV}_3\text{Sb}_5 \) phase. Since the V-based kagome lattice is basically intact, the exotic properties like superconductivity and magnetic frustration are highly expected.

Fig. 1. Crystal structure of \( \text{AV}_3\text{Sb}_5 \), \( \text{AV}_8\text{Sb}_{12} \) and \( \text{AV}_6\text{Sb}_6 \) (\( A=\text{K}, \text{Rb}, \text{Cs} \)). Blue, violent and green balls are \( A \), V and Sb atoms, respectively.

Fig. 2. (a) XRD patterns of \( \text{CsV}_3\text{Sb}_5 \), \( \text{CsV}_8\text{Sb}_{12} \) and \( \text{CsV}_6\text{Sb}_6 \). Right panel shows the zoomed-in peaks (004), (0015) and (008) from \( \sim38^\circ \) to \( \sim40^\circ \).

We have grown the single crystals of three A-V-Sb compounds and put the photo images in the left panel of Fig. 2(a). The typical features are layered structure and shining surface. From the XRD patterns, we can index the lattice constant \( c \) based on the (00\( l \)) peak. The calculated \( c \) values in three compounds are almost identical to the
proposed structure in Fig. 1. Fig. 3 shows the atomic distributions of two new compounds CsV₈Sb₁₂ and CsV₆Sb₆. The false-color image of elemental mapping of AV₈Sb₁₂ is shown in Fig. 3(a), from which we can see the atomic arrangements match the proposed crystal structure of Fig. 1(b). The image of Fig. 3(c) shows the atomic arrangement along the b-axis of CsV₈Sb₁₂. Similarly, the Fig. 3(d) and (e) could match the atomic distributions along the [100] and [110]-axis in CsV₆Sb₆ phase.

Fig. 3. (a) Elemental mapping of CsV₈Sb₁₂ along [001] axis. (b and c) HRTEM images of CsV₈Sb₁₂ along [100] and [010] axis, respectively. (d and e) HRTEM images of CsV₆Sb₆ along [100] and [110] axis, respectively. The blue and pink balls are Cs in CsV₈Sb₁₂ and CsV₆Sb₆, respectively. The violent and green balls are V and Sb, respectively.

We use CsV₈Sb₁₂ and CsV₆Sb₆ to represent the general behavior of the two newly discovered families. Both samples show a metallic behavior from 300 to 2 K without any anomalies observed (Fig. 4a). We have also measured CsV₈Sb₁₂ and CsV₆Sb₆ down to 0.3 K and 100 mK, respectively. No superconductivity can be observed. The residual-resistance ratios (RRR) are generally low, with the highest value of 2.8 for CsV₈Sb₁₂ within the ab plane. The magnetization of CsV₈Sb₁₂ and RbV₆Sb₆ are shown in Fig. 4b. Down to 100 K, both samples show Pauli magnetism. The upturn at low temperatures may originate from magnetic impurities. We note that the overall value of CsV₈Sb₁₂ is around four-fold higher than that of RbV₆Sb₆.
Fig. 4. Electrical transport and magnetization of CsV₈Sb₁₂ and RbV₆Sb₆. (a, b) Temperature-dependent resistivity and magnetization of CsV₈Sb₁₂ and RbV₆Sb₆ within the ab plane and along the c-axis. (c) Temperature-dependent resistance of CsV₈Sb₁₂ under different external pressure. The measured temperature ranges from 2-400 K. We superimposed the resistivity curve at ambient pressure as the dotted line. (d) Carrier concentration and mobility of CsV₈Sb₁₂ against temperature. The recently discovered reentrance of superconductivity in CsV₃Sb₅ provoke us to further investigate the influence of external pressure on the electric transport properties in AV₈Sb₁₂ and AV₆Sb₆. As shown in Fig. 4c, the resistance initially decreases from 2.4 to 4.8 GPa. With further increasing the applied pressure, the resistance gradually increases to a high value. We note that the shape of the RT curve at 2.4 GPa resembles that of resistivity measured at ambient pressure. A prominent feature is the RT curves change from a convex to concave over 10.8 GPa, indicating a dramatic change of the electrical properties. Further measurements down to a lower temperature are tempting to reveal unexpected phenomena.

Fig. 5. X-ray photoelectron spectroscopy (XPS) of V-2p (a) and Sb-3d (b) for CsV₃Sb₅, CsV₆Sb₆, and CsV₈Sb₁₂.
The variation of stacking sequence should be directly reflected in the valence state of the investigated elements. To substantiate the influence of the acquired double-layered kagome compounds, we measured the XPS of CsV$_3$Sb$_5$, CsV$_6$Sb$_6$, and CsV$_8$Sb$_{12}$, as shown in Fig. 5. The peak positions of Cs are identical for all the three compounds at 723.8 eV, indicating that complete loss of out shell electron in all the three compounds. An interesting discovery is the opposite evolution of V’s and Sb’s valence state in CsV$_3$Sb$_5$ and CsV$_8$Sb$_{12}$. In CsV$_6$Sb$_6$, the valence state of V-2p shifts to a lower binding energy, and the peak of Sb-3d remain unchanged. Meanwhile, the valence state of V remains intact in CsV$_8$Sb$_{12}$, which is accompanied by the noticeable peak shift of the Sb-3d towards a higher bonding energy. This dramatic difference lies in the fundamental structure difference in their crystal structures. From Fig. 1, the V$_3$Sb$_5$ kagome layer are identical in both CsV$_3$Sb$_5$ and CsV$_8$Sb$_{12}$, while the building block in CsV$_6$Sb$_6$ evolves into V$_3$Sb$_3$ with the loss of two Sb atoms on one side. This modification of the kagome layer directly alters the valence state of the V. On the contrary, the inserted building block of V$_2$Sb$_2$ in CsV$_8$Sb$_{12}$ connects with the inside V indirectly. Thus, we successfully realize the selective valence modulation in A-V-Sb system through the judicious design of the stacking sequence.

Figure 6.(a,c) ARPES intensity plots at $E_F$ and 0.2 eV below $E_F$ recorded on the (010) surface with $\hbar\nu = 84$ eV. (b,d)DFT calculation at $E_F$ and 0.2 eV below $E_F$. (e,f) ARPES intensity plots showing band dispersions along $\Gamma$-$X$, $\Gamma$-$Y$. (g,h) Calculated band structure along the $\Gamma$-$X$, $\Gamma$-$Y$. (i) 3D bulk Brillouin zone of CsV$_8$Sb$_{12}$. 
To determine the band structure of CsV₈Sb₁₂, we have carried out systematical ARPES measurements on the (001) cleavage surface of CsV₈Sb₁₂ single crystals. We summarized band dispersion and constant energy contours in Fig. 3. In-plane Fermi surface (FS) measured with $h\nu = 84$ eV in Fig. 3a clearly shows the $C_2$ symmetry feature which got verified in the calculated FSs (Fig. 3b), and this testifies that insert V₂Sb₂ layer has strong modulation on the overall band structure. constant energy contours at 0.2 eV (Fig. 3c) below Fermi level has a good agreement with DFT calculation in Fig. 3d. We also measured the band dispersion along $k_x$ (cut #1) and $k_y$ (cut #2), as shown in Fig. 3e and 3f, respectively. These results match our DFT calculations (Fig. 3g and 3h). The absence of the electron bands near the gamma point may be caused by the matrix element effect or possible hole-doping of surface Cs loss.

Due to the V₂Sb₂ layer between kagome layers, the point group of CsV₈Sb₁₂ is $D_{2h}$, where only a two-fold rotational symmetry persists, in contrast to CsV₃Sb₅. Near the Fermi level, the states are dominantly attributed to V 3$d$ orbitals, from both kagome V layer and the intercalated V₂Sb₂ layer. The electron-like band around Gamma point is attributed to ρₚ orbitals of Sb atoms in the kagome layer, similar to CsV₃Sb₅. The two hole-bands around $\Gamma$ point are mainly contributed by the V 3$d$ orbitals in the V₂Sb₂ layer. The band at -0.9 eV around $\Gamma$ point is mainly attributed to V 3$d$ orbitals from both kagome and intercalated layers.

Conclusion
In summary, we have discovered two new families of VSb-based layered compounds, which possess a basic V-kagome lattice similar to that of Known compound AV₃Sb₅. The intercalation of V₂Sb₂ layer and reorganization of half-V₃Sb₅ layer leads to a lower symmetry of $C_2$ (Cmmm) and $C_3$ (R-3m) compare to $C_6$ of AV₃Sb₅. The complex of V-V and V-Sb bonding in three-dimensional space increases the diversity of VSb-based phase. Exertion of physical pressure or chemical substitution may squeeze out more exotic property like superconductivity and CDW. Furthermore, the frustration of magnetism and non-trivial topological phenomena are also highly expected in more V-kagome-based compounds.

References


